## 1. General description

NPN/PNP general-purpose double transistor in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BC847BSH PNP/PNP complement: BC857BSH

## 2. Features and benefits

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- · No mutual interference between the transistors
- High-temperature applications up to 175 °C

## 3. Applications

· General-purpose switching and amplification

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor; for the PNP transistor with negative polarity								
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	45	V	
I <sub>C</sub>	collector current			-	-	100	mA	
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$		200	300	450		



#### 45 V, 100 mA NPN/PNP general-purpose double transistor

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	□6 □5 □4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2		(TR1) TR2)
4	E2	emitter TR2	H <sub>1</sub> H <sub>2</sub> H <sub>3</sub>	
5	B2	base TR2	TSSOP6 (SOT363)	
6	C1	collector TR1		sym139

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BC847BPNH		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
BC847BPNH	7E%

<sup>[1] % =</sup> placeholder for manufacturing site code

## 8. Limiting values

#### Table 5. Limiting values

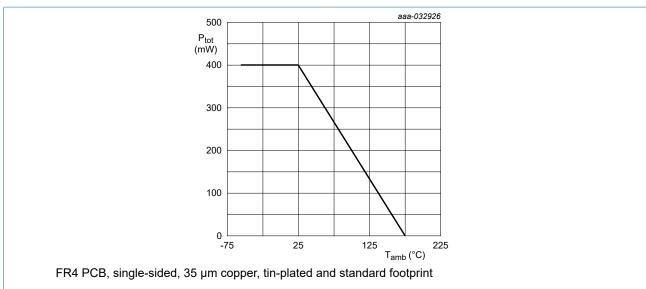
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or; for the PNP transistor wit	h negative polarity	'			
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	200	mA
I <sub>BM</sub>	peak base current			-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	270	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	400	mW
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

BC847BPNH

#### 45 V, 100 mA NPN/PNP general-purpose double transistor



### Fig. 1. Per device: Power derating curve

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions			Min	Тур	Max	Unit
Per transiste	or		,					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	]	-	-	556	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point				-	-	170	K/W
Per device								
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	]	-	-	375	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

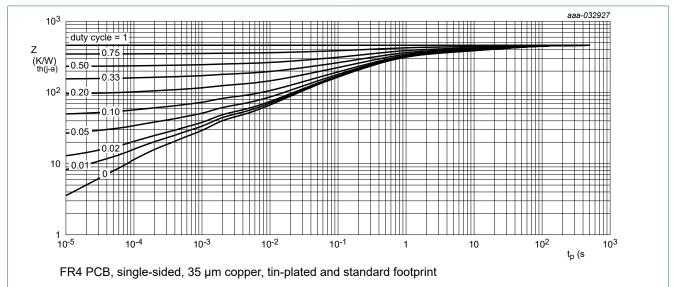


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

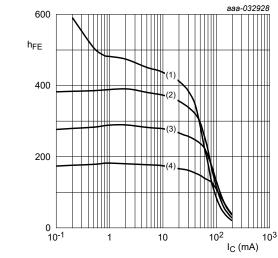
### 45 V, 100 mA NPN/PNP general-purpose double transistor

## 10. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or; for the PNP transistor	with negative polarity					
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = 100 μA; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		45	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage	I <sub>C</sub> = 0 A; I <sub>E</sub> = 100 μA; T <sub>amb</sub> = 25 °C		7	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	15	nA
	current	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 7 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C		200	300	450	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C		-	50	100	mV
	saturation voltage	$I_C$ = 100 mA; $I_B$ = 5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	200	300	mV
V <sub>BEsat</sub> base-emitter saturation	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C	[1]	-	750	850	mV	
	voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA; T <sub>amb</sub> = 25 °C		-	875	-	mV
V <sub>BE</sub> base-emitter voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C	[2]	600	655	700	mV	
		V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C	[2]	-	705	770	mV
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C		100	-	-	MHz
NF	noise figure	$V_{CE}$ = 5 V; $I_{C}$ = 0.2 mA; $R_{S}$ = 2 k $\Omega$ ; f = 10 Hz to 15.7 kHz; $T_{amb}$ = 25 °C		-	1.7	-	dB
TR1 (NPN)				·			
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	1.2	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	11	-	pF
NF	noise figure	$V_{CE}$ = 5 V; $I_{C}$ = 0.2 mA; $R_{S}$ = 2 k $\Omega$ ; $f$ = 1 kHz; $B$ = 200 Hz; $T_{amb}$ = 25 °C		-	3.1	-	dB
TR2 (PNP)							1
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	1.8	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB}$ = -0.5 V; $I_{C}$ = 0 A; $i_{c}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	8.5	-	pF
NF	noise figure	$V_{CE}$ = -5 V; $I_{C}$ = -0.2 mA; $R_{S}$ = 2 k $\Omega$ ; $I_{C}$ = 1 kHz; $I_{C}$ = 200 Hz; $I_{C}$ $I_{C}$ = 25 °C		-	3.3	-	dB

V<sub>BEsat</sub> decreases by about 1.7 mV/K with increasing temperature.
V<sub>BE</sub> decreases by about 2 mV/K with increasing temperature.

#### 45 V, 100 mA NPN/PNP general-purpose double transistor

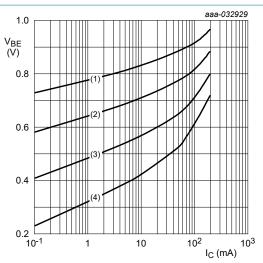


 $V_{CE} = 5 V$ (1)  $T_{amb} = 175 °C$ 

(2) T<sub>amb</sub> = 150 °C

(3)  $T_{amb} = 25 ^{\circ}C$ (4)  $T_{amb} = -40 ^{\circ}C$ 

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values

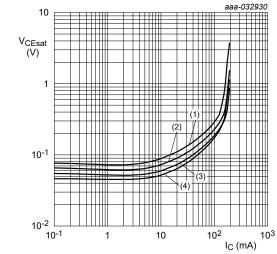


V<sub>CE</sub> = 5 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

(4)  $T_{amb} = 175^{\circ}C$ 

TR1 (NPN): Base-emitter voltage as a function Fig. 4. of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

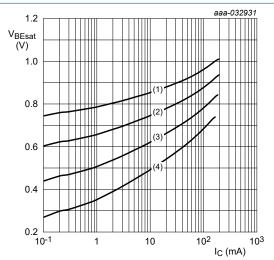
 $(1) T_{amb} = 175 °C$ 

(2) T<sub>amb</sub> = 100 °C

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

(4)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 5. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



 $I_C/I_B = 20$ 

(1) T<sub>amb</sub> = -40 °C

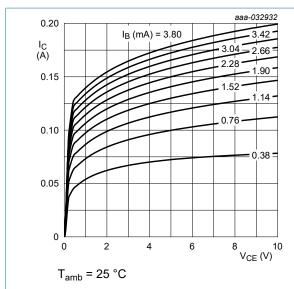
(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

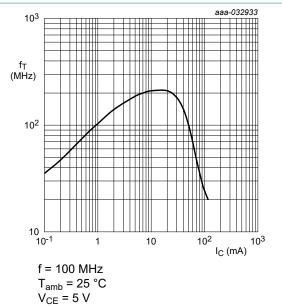
(4)  $T_{amb} = 175 \, ^{\circ}C$ 

Fig. 6. TR1 (NPN): Base-emitter saturation voltage as a function of collector current; typical values

#### 45 V, 100 mA NPN/PNP general-purpose double transistor



TR1 (NPN): Collector current as a function of Fig. 7. collector-emitter voltage; typical values



T<sub>amb</sub> = 25 °C

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values

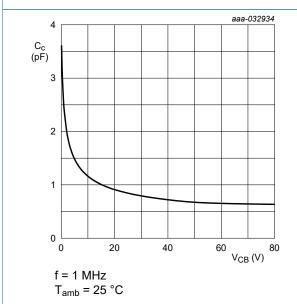


Fig. 9. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values

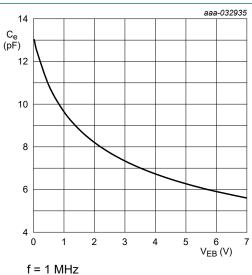
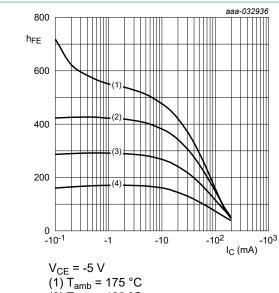


Fig. 10. TR1 (NPN): Emitter capacitance as a function of emitter-base voltage; typical values

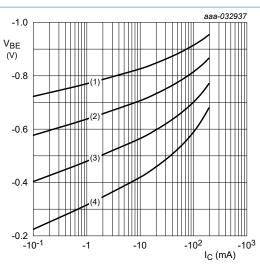
#### 45 V, 100 mA NPN/PNP general-purpose double transistor



(2)  $T_{amb} = 100 \, ^{\circ}C$ 

(3)  $T_{amb} = 25 ^{\circ}C$ (4)  $T_{amb} = -40 ^{\circ}C$ 

Fig. 11. TR2 (PNP): DC current gain as a function of collector current; typical values

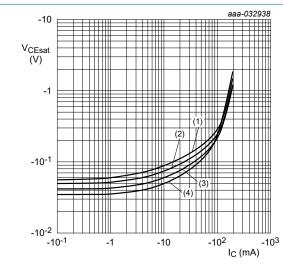


V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

(4)  $T_{amb} = 175 \, ^{\circ}C$ 

Fig. 12. TR2 (PNP): Base-emitter voltage as a function of collector current; typical value



 $I_{\rm C}/I_{\rm B} = 20$ 

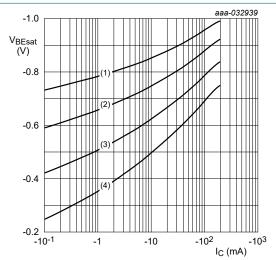
 $(1) T_{amb} = 175 °C$ 

(2) T<sub>amb</sub> = 100 °C

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

(4)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 13. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

(4)  $T_{amb} = 175 \, ^{\circ}C$ 

Fig. 14. TR2 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

#### 45 V, 100 mA NPN/PNP general-purpose double transistor

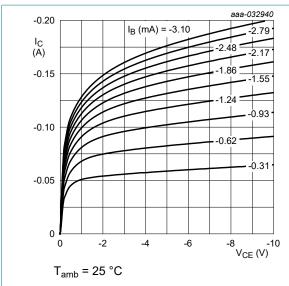
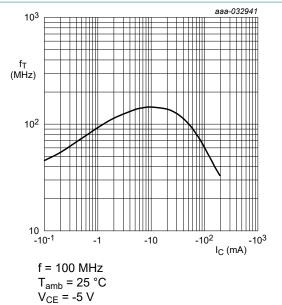


Fig. 15. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values



T<sub>amb</sub> = 25 °C

Fig. 16. TR2 (PNP): Transition frequency as a function of collector current; typical values

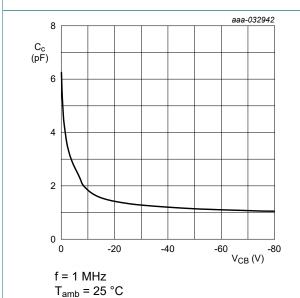


Fig. 17. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

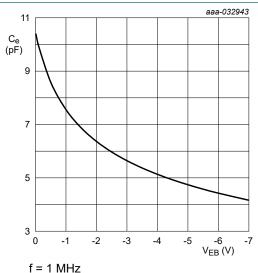
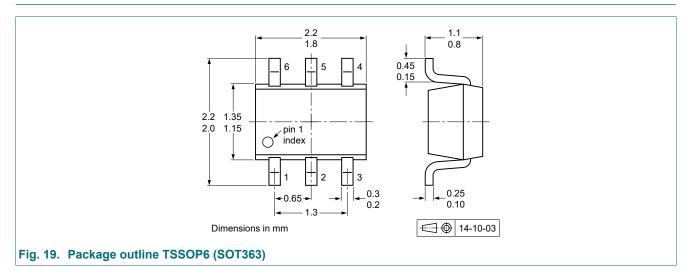


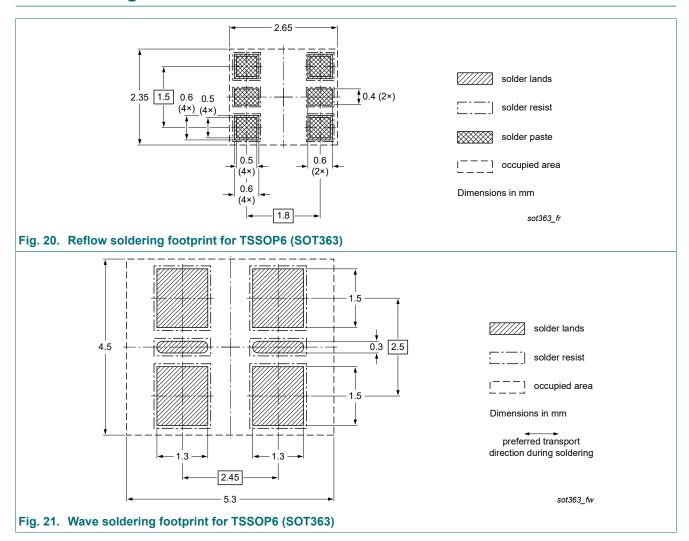
Fig. 18. TR2 (PNP): Emitter capacitance as a function of emitter-base voltage; typical values

#### 45 V, 100 mA NPN/PNP general-purpose double transistor

# 11. Package outline



## 12. Soldering



## 45 V, 100 mA NPN/PNP general-purpose double transistor

# 13. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847BPNH v.1	20210504	Product data sheet	-	-

#### 45 V, 100 mA NPN/PNP general-purpose double transistor

## 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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BC847BPNH

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### 45 V, 100 mA NPN/PNP general-purpose double transistor

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